WHAT IS CLAIMED IS:

1. A solid state image pickup device comprising:

a conductive pattern formed above a substrate,

an insulating film provided above said substrate in the state of covering said conductive pattern, and

a metallic pattern formed above said insulating film and making contact with said conductive pattern through a contact window formed in said insulating film, wherein

said metallic pattern at said contact window contains at least one of silicon metal oxide or silicon metal nitride.

2. A solid state image pickup device comprising:

an insulating film provided above a substrate, and

a metallic pattern formed above said insulating film and making contact with said substrate through a contact window formed in said insulating film, wherein

said metallic pattern at said contact window contains at least one of silicon metal oxide or silicon metal nitride.

3. The solid state image pickup device as set forth in claim 1, wherein

said metallic pattern is provided as a shunt wiring for impressing a voltage on said conductive pattern, and

said substrate is comprised of silicon.

4. The solid state image pickup device as set forth in claim 2, wherein

said metallic pattern is provided as a light shielding film, and

said substrate is comprised of silicon.

5. The solid state image pickup device as set forth in claim 1, wherein

an in-layer lens having a planarized surface is provided above the upper side of said substrate.

6. The solid state image pickup device as set forth in claim 1, wherein

the metal of said metallic pattern is the same as said metal.

7. The solid state image pickup device as set forth in claim 2, wherein

the metal of said metallic pattern is the same as said metal.

8. The solid state image pickup device as set forth in claim 1, wherein

said metal is a high melting point metal.

9. The solid state image pickup device as set forth in claim 2, wherein

said metal is a high melting point metal.

10. A method of fabricating a solid state image pickup device, comprising the steps of:

providing an insulating film covering a conductive pattern formed above a substrate with a contact window reaching said conductive pattern,

covering the bottom surface of said contact window with a thin film comprised of at least one of silicon oxide and silicon nitride,

forming a metallic pattern above said insulating film and in said contact window, and

performing a heat treatment to cause said thin film and said metallic pattern to react with each other.

11. A method of fabricating a solid state image pickup device, comprising the steps of:

providing an insulating film formed above a substrate with a contact window reaching said substrate,

covering the bottom surface of said contact window with a thin film comprised of at least one of silicon oxide and silicon nitride,

forming a metallic pattern above said insulating film and in said contact window, and

performing a heat treatment to cause said thin film and said metallic pattern to react with each other.

12. The method of fabricating a solid state image

pickup device as set forth in claim 10, wherein

said substrate is comprised of silicon, and

said metallic pattern is formed as a shunt wiring for impressing a voltage on said conductive pattern.

13. The method of fabricating a solid state image pickup device as set forth in claim 11, wherein

said substrate is comprised of silicon, and

said metallic pattern is formed as a light shielding film.

14. The method of fabricating a solid state image pickup device as set forth in claim 10, wherein

the interfacial level of said substrate is lowered in the step of performing said heat treatment.

15. The method of fabricating a solid state image pickup device as set forth in claim 11, wherein

the interfacial level of said substrate is lowered in the step of performing said heat treatment.

16. The method of fabricating a solid state image pickup device as set forth in claim 10, wherein

a step of forming a fluid insulating film in the state of covering said metallic pattern is conducted after said metallic pattern is formed, and

reflow of said fluid insulating film is effected to bring said fluid insulating film into a lens shape in the

step of performing said heat treatment.

17. The method of fabricating a solid state image pickup device as set forth in claim 11, wherein

a step of forming a fluid insulating film in the state of covering said metallic pattern is conducted after said metallic pattern is formed, and

reflow of said fluid insulating film is effected to bring said fluid insulating film into a lens shape in the step of performing said heat treatment.

18. The method of fabricating a solid image pickup device as set forth in claim 10, wherein

said thin film is so formed as to cover the inside wall of said contact window in the step of forming said thin film.

19. The method of fabricating a solid state image pickup device as set forth in claim 11, wherein

said thin film is so formed as to cover the inside wall of said contact window in the step of forming said thin film.

20. The method of fabricating a solid state image pickup device as set forth in claim 10, wherein

said metallic pattern is formed by use of a high melting point metal.

21. The method of fabricating a solid state image

pickup device as set forth in claim 11, wherein

said metallic pattern is formed by use of a high melting point metal.